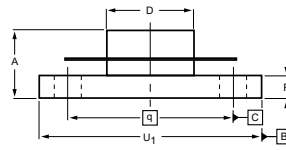


DESCRIPTION

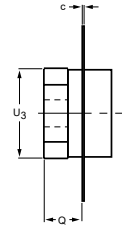
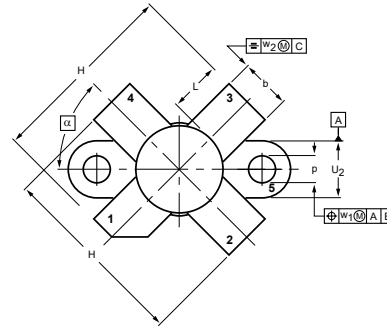
Silicon N-channel enhancement mode vertical D-MOS transistor is designed for broadband HF applications.

FEATURES

- Output Power: 30 W
- Power Gain: 22 dB Typ@30M, 50V
- Efficiency: 55% Typ@30M, 50V



1. Drain
2. Source
3. Gate
4. Source
5. FIN



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.20 6.10	5.82 5.56	0.18 0.10	10.20 9.70	2.92 2.61	20.71 19.93	5.61 5.16	3.33 3.04	4.63 4.11	18.42	25.15 24.38	6.61 6.09	9.78 9.39	0.51	1.02	45°
inches	0.283 0.240	0.229 0.219	0.007 0.004	0.401 0.382	0.115 0.103	0.815 0.785	0.221 0.203	0.131 0.120	0.182 0.162	0.725	0.99 0.96	0.26 0.24	0.385 0.370	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V _{DSS}	125	V
Drain-Gate Voltage	V _{DGR}	125	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current — Continuous	I _D	6	A
Total Device Dissipation	P _D	170	W
Junction Temperature	T _J	200	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =10mA, V _{GS} =0	125	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =50V	-	-	1	mA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V	-	-	1	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 10 V, I _D = 10mA	1.0	2.5	5.0	V
Drain-Source On-Voltage	V _{DS(on)}	V _{GS} = 10 V, I _D = 2.5A	1.0	3.5	5.0	V
Forward Transconductance	g _{fs}	V _{DS} = 10 V, I _D = 2.5A	0.8	1.2	-	mhos
Input Capacitance	C _{iss}	V _{DS} = 28 V, V _{GS} = 0 V, f = 1.0 MHz	-	65	-	pF
Output Capacitance	C _{oss}		-	40	-	pF
Reverse Transfer Capacitance	C _{rss}		-	5.5	-	pF
Common Source Power Gain	G _{PS}	V _{DD} =50V, P _{OUT} =30W,	18.0	22.0	-	dB
Drain Efficiency	η _D	f=30MHz, I _{DQ} = 100 mA	50	55.0	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.